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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/664,146	09/17/2003	Hongyong Zhang	1117.68308	3479	
759	90 06/14/2004		EXAM	EXAMINER	
Patrick G. Burns			SMOOT, STEPHEN W		
Greer, Burns &	Crain, Ltd.				
Suite 2500		ART UNIT	PAPER NUMBER		
300 South Wack	er Drive	2813			
Chicago, IL 60	0606				
			DATE MAILED: 06/14/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

					44			
		Application 1	No.	Applicant(s)				
Office Action Summary		10/664,146		ZHANG ET AL.				
		Examiner		Art Unit				
		Stephen W. S		2813				
Th MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply								
THE   - External after - If the - If NC - Failu Any (	ORTENED STATUTORY PERIOD FOR R MAILING DATE OF THIS COMMUNICATION in the major of 37 C SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days, in period for reply is specified above, the maximum statutory perion of the period for reply within the set or extended period for reply will, by reply received by the Office later than three months after the end patent term adjustment. See 37 CFR 1.704(b).	ON. FR 1.136(a). In no event, hon. a reply within the statutory period will apply and will exp statute, cause the application	nowever, may a reply be time minimum of thirty (30) days bire SIX (6) MONTHS from on to become ABANDONEI	nely filed s will be considered timel the mailing date of this or D (35 U.S.C. § 133).	y. ommunication.			
Status								
1)[	Responsive to communication(s) filed on	17 September 200	<u>3</u> .					
· · · · · · · · · · · · · · · · · · ·	This action is <b>FINAL</b> . 2b) This action is non-final.							
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposit	ion of Claims							
5)⊠ 6)⊠ 7)□ 8)□	4)  Claim(s) <u>22-35</u> is/are pending in the application.  4a) Of the above claim(s) is/are withdrawn from consideration.  5)  Claim(s) <u>28,29 and 31</u> is/are allowed.							
Applicat	ion Papers							
10)⊠	The specification is objected to by the Exact The drawing(s) filed on <u>17 September 200</u> Applicant may not request that any objection to Replacement drawing sheet(s) including the or The oath or declaration is objected to by the	03 is/are: a)☐ acce o the drawing(s) be h orrection is required i	eld in abeyance. Seef f the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 Cl	FR 1.121(d).			
Priority (	ınder 35 U.S.C. § 119							
<ul> <li>12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No. 09/277,880.</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>								
2) Notice 3) Information	t(s) re of References Cited (PTO-892) re of Draftsperson's Patent Drawing Review (PTO-94 mation Disclosure Statement(s) (PTO-1449 or PTO/S rr No(s)/Mail Date <u>9-17-03</u> .	6B/08) 5)	Interview Summary Paper No(s)/Mail Da Notice of Informal F	ate	O-152)			

Application/Control Number: 10/664,146 Page 2

Art Unit: 2813

#### **DETAILED ACTION**

This Office action is in response to application papers filed on 17 September 2003.

## Drawings

1. The proposed drawing correction to Fig. 8A filed on 17 September 2003 is approved. A replacement drawing sheet featuring this correction is required in reply to the Office action to avoid abandonment of the application. The requirement for corrected drawings will not be held in abeyance.

## Specification

2. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The following title is suggested: CMOS-Type Thin Film Semiconductor Device and Method of Fabricating the Same.

Application/Control Number: 10/664,146 Page 3

Art Unit: 2813

3. The lengthy specification has not been checked to the extent necessary to determine the presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

4. The disclosure is objected to because of the following informality:

Update the first sentence of the specification to indicate that US Application Serial Number 09/277,880 is now US Patent Number 6,635,521.

Appropriate correction is required.

#### Claim Rejections - 35 USC § 112

- 5. The following is a quotation of the second paragraph of 35 U.S.C. 112:
  The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 6. Claims 22-27, 30, 32-35 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 22, lines 8-11, the term "including CMOS transistors each of which comprises p- and n- type thin film transistors and which have different operating voltages" does not particularly point out if each CMOS transistor has a different

Application/Control Number: 10/664,146

Art Unit: 2813

operating voltage or if the operating voltage corresponding to the p-type transistors is different from that corresponding to the n-type transistors.

In claim 23, lines 8-11, the term "including CMOS transistors each of which comprises p- and n- type thin film transistors and which have different operating voltages" does not particularly point out if each CMOS transistor has a different operating voltage or if the operating voltage corresponding to the p-type transistors is different from that corresponding to the n-type transistors.

Claim 23 recites the limitation "the other part" in line 30. There is insufficient antecedent basis for this limitation in claim 23.

Claims 24-27 are rejected under 35 U.S.C. 112, second paragraph, because they depend on claim 23.

Claim 30 recites the limitation "the difference in width" in line 8. There is insufficient antecedent basis for this limitation claim 30.

In claim 32, lines 9-12, the term "comprising CMOS transistors in each of which p- and n- type thin film transistors are formed and which have different operating voltages" does not particularly point out if each CMOS transistor has a different operating voltage or if the operating voltage corresponding to the p-type transistors is different from that corresponding to the n-type transistors.

In claim 33, lines 9-12, the term "comprising CMOS transistors in each of which p- and n- type thin film transistors are formed and which have different operating voltages" does not particularly point out if each CMOS transistor has a different

operating voltage or if the operating voltage corresponding to the p-type transistors is different from that corresponding to the n-type transistors.

Claims 34-35 are rejected under 35 U.S.C. 112, second paragraph, because they depend on claim 32.

## Allowable Subject Matter

- 7. Claims 28-29, 31 are allowed.
- 8. The following is a statement of reasons for the indication of allowable subject matter: Claims 28-29, 31 are allowed because the prior art of record does not teach or suggest, in combination with the other claim limitations, a CMOS device that features p-type thin film transistors with p-doped channel regions and n-type thin film transistors with p-doped channel regions, wherein the channel regions corresponding to the n-type thin film transistors have a higher concentration of p-type impurities.

#### Conclusion

9. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Yamazaki et al. ('876), Oka et al., and Takenaka (JP 9-270521 A), teach thin film transistors that feature a non-selectively boron-doped active layer. Yamazaki et al. ('132) teach a CMOS structure that features a selectively boron-doped

Art Unit: 2813

active layer corresponding to a p-type thin film transistor. Takenaka (JP 9-186343 A) teaches a CMOS structure that features a selectively boron-doped active layer corresponding to an n-type thin film transistor.

Any inquiry concerning this communication or earlier communications from the 10. examiner should be directed to Stephen W. Smoot whose telephone number is 571-272-1698. The examiner can normally be reached on M-F (8:00am to 4:30pm).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr. can be reached on 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

**SWS** 

Stephen W. Smoot Patent Examiner Art Unit 2813